

# Voltage Regulator - Low Dropout

#### 300 mA

## MC33275, NCV33275

The MC33275 series are micropower low dropout voltage regulators available in a wide variety of output voltages as well as packages, SOT-223, SOP-8, DPAK, and DFN 4x4 surface mount packages. These devices feature a very low quiescent current and are capable of supplying output currents up to 300 mA. Internal current and thermal limiting protection are provided by the presence of a short circuit at the output and an internal thermal shutdown circuit.

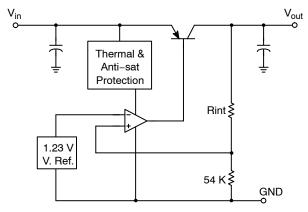
Due to the low input-to-output voltage differential and bias current specifications, these devices are ideally suited for battery powered computer, consumer, and industrial equipment where an extension of useful battery life is desirable.

#### **Features**

- Low Input–to–Output Voltage Differential of 25 mV at  $I_O$  = 10 mA, and 260 mV at  $I_O$  = 300 mA
- Extremely Tight Line and Load Regulation
- Stable with Output Capacitance of only 0.33  $\mu F$  for 2.5 V Output Voltage
- Internal Current and Thermal Limiting
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

#### **Applications**

- Battery Powered Consumer Products
- Hand-Held Instruments
- Camcorders and Cameras



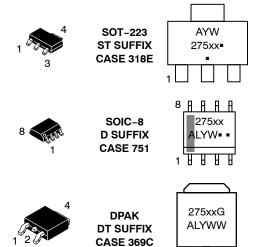
This device contains 41 active transistors

Figure 1. Simplified Block Diagram

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# LOW DROPOUT MICROPOWER VOLTAGE REGULATOR

#### **MARKING DIAGRAMS**





DFN-8, 4x4 MN SUFFIX CASE 488AF



xx = Voltage Version
A = Assembly Location
L = Wafer Lot

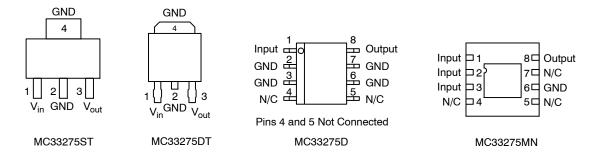
L = Wafer Lot Y = Year W, WW = Work Week • or G = Pb-Free Device

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 10 of this data sheet.

#### **PIN CONNECTIONS**



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Input Voltage	V <sub>CC</sub>	13	Vdc
Power Dissipation and Thermal Characteristics $T_{\Delta} = 25^{\circ}C$			
Maximum Power Dissipation Case 751 (SOIC–8) D Suffix	$P_{D}$	Internally Limited	W
Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case Case 318E (SOT-223) ST Suffix	${\sf R}_{\sf  heta JA} \ {\sf R}_{\sf  heta JC}$	160 25	°C/W
Thermal Resistance, Junction-to-Air Thermal Resistance, Junction-to-Case Case 369A (DPAK-3) DT Suffix	$R_{ hetaJA} \ R_{ hetaJC}$	245 15	°C/W
Thermal Resistance, Junction-to-Air Thermal Resistance, Junction-to-Case Case 488AF (DFN-8, 4x4) MN Suffix	$R_{ heta JA} \ R_{ heta JC}$	92 6.0	°C/W °C/W
Thermal Resistance, Junction-to-Air (with 1.0 oz PCB cu area) Thermal Resistance, Junction-to-Air (with 1.8 oz PCB cu area) Thermal Resistance, Junction-to-Case	R <sub>θJA</sub> R <sub>θJA</sub> psi–JC*	183 93 9.0	°C/W °C/W
Output Current	lo	300	mA
Maximum Junction Temperature	TJ	150	°C
Operating Ambient Temperature Range	T <sub>A</sub>	- 40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	- 65 to +150	°C
Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Machine Model (MM)	ESD	4000 400	٧

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

<sup>\*&</sup>quot;C" ("case") is defined as the solder–attach interface between the center of the exposed pad on the bottom of the package, and the board to which it is attached.

### $\textbf{ELECTRICAL CHARACTERISTICS} \ (C_L = 1.0 \mu F, \ T_A = 25 ^{\circ}C, \ for \ min/max \ values \ T_J = -40 ^{\circ}C \ to \ +125 ^{\circ}C, \ Note \ 1)$

	Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage 2.5 V Suffix 3.0 V Suffix 3.3 V Suffix 5.0 V Suffix	$I_O = 0$ mA to 250 mA $T_A = 25^{\circ}\text{C}$ , $V_{in} = [V_O + 1] \text{ V}$	Vo	2.475 2.970 3.267 4.950	2.50 3.00 3.30 5.00	2.525 3.030 3.333 5.05	Vdc
2.5 V Suffix 3.0 V Suffix 3.3 V Suffix 5.0 V Suffix	$V_{in} = [V_O + 1] V$ , $0 < I_O < 100 \text{ mA}$ 2% Tolerance from $T_J = -40 \text{ to } +125^{\circ}\text{C}$		2.450 2.940 3.234 4.900	- - -	2.550 3.060 3.366 5.100	
Line Regulation	$V_{in}$ = [ $V_O$ + 1] V to 12 V, $I_O$ = 250 mA, All Suffixes $T_A$ = 25°C	Reg <sub>line</sub>	-	2.0	10	mV
Load Regulation	$V_{in}$ = [ $V_O$ + 1] V, $I_O$ = 0 mA to 250 mA, All Suffixes $T_A$ = 25°C	Reg <sub>load</sub>	-	5.0	25	mV
Dropout Voltage $I_O = 10 \text{ mA}$ $I_O = 100 \text{ mA}$ $I_O = 250 \text{ mA}$ $I_O = 300 \text{ mA}$	$T_J = -40$ °C to +125°C	V <sub>in</sub> – V <sub>O</sub>	- - - -	25 115 220 260	100 200 400 500	mV
Ripple Rejection (	(120 Hz) V <sub>in(peak-peak)</sub> = [V <sub>O</sub> + 1.5] V to [V <sub>O</sub> + 5.5] V	-	65	75	-	dB
Output Noise Voltage $C_L = 1.0~\mu\text{F} \qquad I_O = 50~\text{mA}~(10~\text{Hz to}~100~\text{kHz}) \\ C_L = 200~\mu\text{F}$		V <sub>n</sub>	- -	160 46	<u>-</u>	μVrms
CURRENT PARAM	METERS					
Quiescent Curren	t ON Mode $V_{in} = [V_O + 1] V, I_O = 0 \text{ mA}$	I <sub>QOn</sub>	-	125	200	μΑ

Quiescent Current ON Mode	$V_{in} = [V_O + 1] V, I_O = 0 mA$	I <sub>QOn</sub>	-	125	200	μΑ
Quiescent Current ON Mode SAT 3.0 V Suffix 3.3 V Suffix 5.0 V Suffix	$V_{in} = [V_O - 0.5] V, I_O = 0 \text{ mA (Notes 2, 3)}$	I <sub>QSAT</sub>	- - -	1500 1500 1500	2000 2000 2000	μΑ
Current Limit	V <sub>in</sub> = [V <sub>O</sub> + 1] V, V <sub>O</sub> Shorted	I <sub>LIMIT</sub>	_	450	_	mA

#### THERMAL SHUTDOWN

Thermal Shutdown	_	-	150	_	°C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Low duty pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
   Quiescent Current is measured where the PNP pass transistor is in saturation. V<sub>in</sub> = [V<sub>O</sub> 0.5] V guarantees this condition.
- 3. For 2.5 V version, I<sub>QSAT</sub> is constrained by the minimum input voltage of 2.5 V.

#### **DEFINITIONS**

**Load Regulation** – The change in output voltage for a change in load current at constant chip temperature.

**Dropout Voltage** – The input/output differential at which the regulator output no longer maintains regulation against further reductions in input voltage. Measured when the output drops 100 mV below its nominal value (which is measured at 1.0 V differential), dropout voltage is affected by junction temperature, load current and minimum input supply requirements.

**Output Noise Voltage** – The RMS AC voltage at the output with a constant load and no input ripple, measured over a specified frequency range.

**Maximum Power Dissipation** – The maximum total dissipation for which the regulator will operate within specifications.

**Quiescent Current** – Current which is used to operate the regulator chip and is not delivered to the load.

**Line Regulation** – The change in output voltage for a change in the input voltage. The measurement is made under conditions of low dissipation or by using pulse techniques such that the average chip temperature is not significantly affected.

**Maximum Package Power Dissipation** – The maximum package power dissipation is the power dissipation level at which the junction temperature reaches its maximum value i.e.  $150^{\circ}$ C. The junction temperature is rising while the difference between the input power ( $V_{CC} \times I_{CC}$ ) and the output power ( $V_{out} \times I_{out}$ ) is increasing.

Depending on ambient temperature, it is possible to calculate the maximum power dissipation and so the maximum current as following:

$$Pd = \frac{T_J - T_A}{R_{\theta,JA}}$$

The maximum operating junction temperature  $T_J$  is specified at 150°C, if  $T_A = 25$ °C, then  $P_D$  can be found. By neglecting the quiescent current, the maximum power dissipation can be expressed as:

$$I_{out} = \frac{P_D}{V_{CC} - V_{out}}$$

The thermal resistance of the whole circuit can be evaluated by deliberately activating the thermal shutdown of the circuit (by increasing the output current or raising the input voltage for example).

Then you can calculate the power dissipation by subtracting the output power from the input power. All variables are then well known: power dissipation, thermal shutdown temperature and ambient temperature.

$$R_{\theta JA} = \frac{T_J - T_A}{P_D}$$

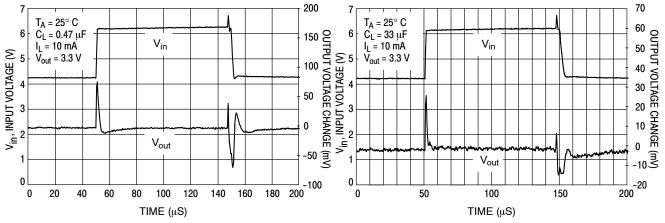


Figure 2. Line Transient Response

**Figure 3. Line Transient Response** 

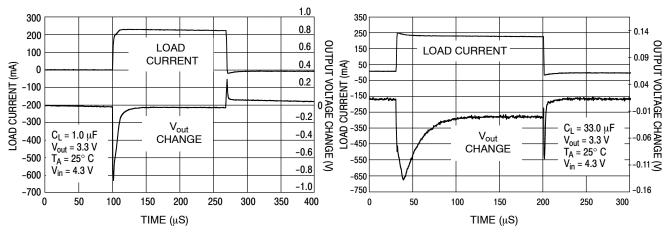


Figure 4. Load Transient Response

Figure 5. Load Transient Response

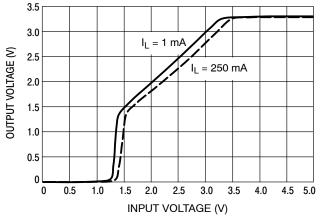


Figure 6. Output Voltage versus Input Voltage

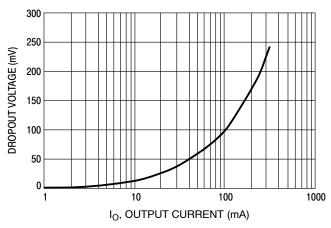


Figure 7. Dropout Voltage versus Output Current

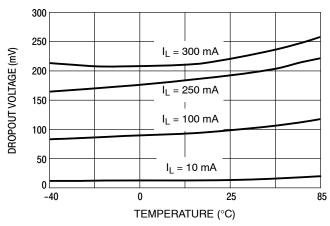


Figure 8. Dropout Voltage versus Temperature

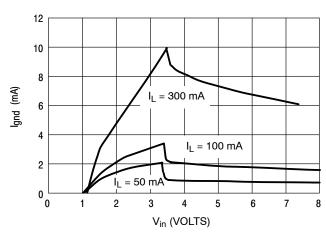


Figure 9. Ground Pin Current versus Input Voltage

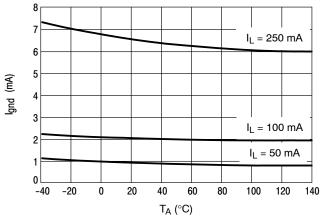


Figure 10. Ground Pin Current versus Ambient Temperature

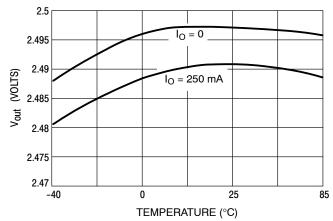


Figure 11. Output Voltage versus Ambient Temperature ( $V_{in} = V_{out} + 1V$ )

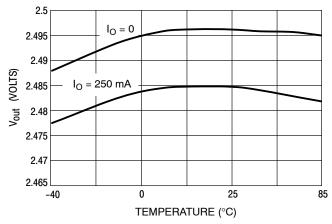


Figure 12. Output Voltage versus Ambient Temperature (V<sub>in</sub> = 12 V)

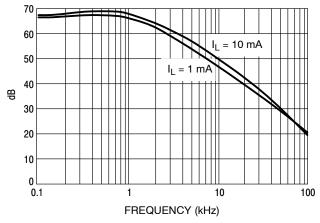


Figure 13. Ripple Rejection

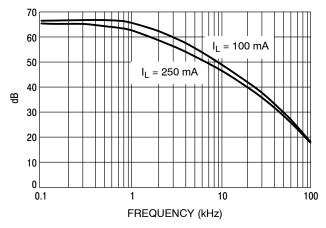


Figure 14. Ripple Rejection

#### **APPLICATIONS INFORMATION**

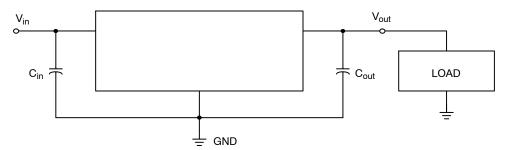


Figure 15. Typical Application Circuit

The MC33275 regulators are designed with internal current limiting and thermal shutdown making them user-friendly. Figure 15 is a typical application circuit. The output capability of the regulator is in excess of 300 mA, with a typical dropout voltage of less than 260 mV. Internal protective features include current and thermal limiting.

#### **EXTERNAL CAPACITORS**

These regulators require only a 0.33 µF (or greater) capacitance between the output and ground for stability for 1.8 V, 2.5 V, 3.0 V, and 3.3 V output voltage options. Output voltage options of 5.0 V require only 0.22 µF for stability. The output capacitor must be mounted as close as possible to the MC33275. If the output capacitor must be mounted further than two centimeters away, then a larger value of output capacitor may be required for stability. A value of 0.68 µF or larger is recommended. Most type of aluminum, tantalum, or multilayer ceramic will perform adequately. Solid tantalums or appropriate multilayer ceramic capacitors are recommended for operation below 25°C. An input bypass capacitor is recommended to improve transient response or if the regulator is connected to the supply input filter with long wire lengths, more than 4 inches. This will reduce the circuit's sensitivity to the input line impedance at high frequencies. A 0.33 µF or larger tantalum, mylar, ceramic, or other capacitor having low internal impedance at high frequencies should be chosen. The bypass capacitor should be mounted with shortest possible lead or track length directly across the regulator's input terminals. Figure 16 shows the ESR that allows the LDO to remain stable for various load currents.

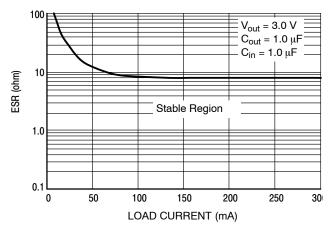


Figure 16. ESR for V<sub>out</sub> = 3.0V

## Applications should be tested over all operating conditions to insure stability.

#### THERMAL PROTECTION

Internal thermal limiting circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When activated, typically at 150°C, the output is disabled. There is no hysteresis built into the thermal protection. As a result the output will appear to be oscillating during thermal limit. The output will turn off until the temperature drops below the 150°C then the output turns on again. The process will repeat if the junction increases above the threshold. This will continue until the existing conditions allow the junction to operate below the temperature threshold.

## Thermal limit is not a substitute for proper heatsinking.

The internal current limit will typically limit current to 450 mA. If during current limit the junction exceeds 150°C, the thermal protection will protect the device also. **Current limit is not a substitute for proper heatsinking.** 

#### **OUTPUT NOISE**

In many applications it is desirable to reduce the noise present at the output. Reducing the regulator bandwidth by increasing the size of the output capacitor will reduce the noise.

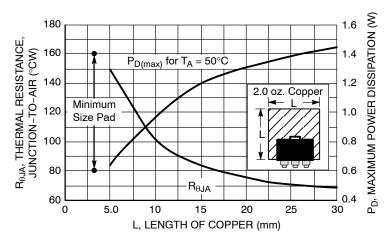


Figure 17. SOT-223 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

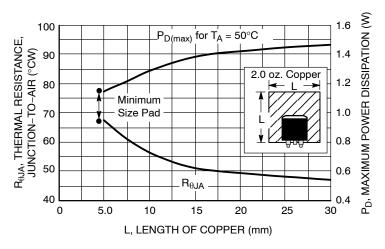


Figure 18. DPAK Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

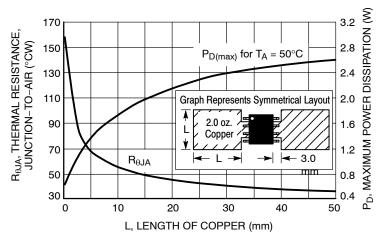


Figure 19. SOP-8 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

#### **ORDERING INFORMATION**

Device	V <sub>O</sub> Typ (V)	Operating Temperature Range, Tolerance	Case	Package	Marking	Shipping <sup>†</sup>
MC33275DT-2.5RKG	2.5 V (Fixed Voltage)	1% Tolerance at T <sub>A</sub> = 25°C	369A	DPAK (Pb-Free)	27525G	2500/Tape & Reel
MC33275D-3.0R2G	3.0 V (Fixed Voltage)		751	SOIC-8 (Pb-Free)	27530	2500/Tape & Reel
MC33275MN-3.0R2G		2% Tolerance at T <sub>J</sub> from -40°C to +125°C	488AF	DFN8 (Pb-Free)	27530	3000/Tape & Reel
MC33275D-3.3R2G	3.3 V (Fixed Voltage)	1% Tolerance at T <sub>A</sub> = 25°C	751	SOIC-8 (Pb-Free)	27533	2500/Tape & Reel
MC33275DT-3.3RKG			369A	DPAK (Pb-Free)	27533G	2500/Tape & Reel
MC33275ST-3.3T3G		2% Tolerance at	318E	SOT-223 (Pb-Free)	27533	4000/Tape & Reel
NCV33275ST3.3T3G*		T <sub>J</sub> from -40°C to +125°C 1% Tolerance at T <sub>A</sub> = 25°C	318E	SOT-223 (Pb-Free)	27533	4000/Tape & Reel
MC33275D-5.0R2G	5.0 V (Fixed Voltage)	1% Tolerance at T <sub>A</sub> = 25°C	751	SOIC-8 (Pb-Free)	27550	2500/Tape & Reel
MC33275DT-5.0RKG			369A	DPAK (Pb-Free)	27550G	2500/Tape & Reel
MC33275ST-5.0T3G		2% Tolerance at T <sub>J</sub> from -40°C to +125°C 1% Tolerance at T <sub>A</sub> = 25°C	318E	SOT-223 (Pb-Free)	27550	4000/Tape & Reel
NCV33275ST-5.0T3G*			318E	SOT-223 (Pb-Free)	27550	4000/Tape & Reel

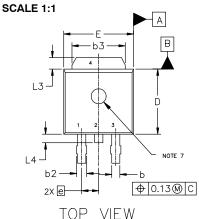
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

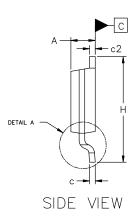
<sup>&</sup>quot;NCV Prenx for Automotive and Other Applications Requiring Onlique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable



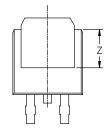
#### DPAK3 6.10x6.54x2.28, 2.29P CASE 369C **ISSUE J**

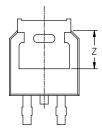
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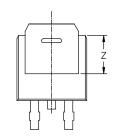


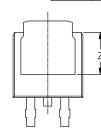


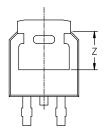
MILLIMETERS				
DIM	MIN	NOM	MAX	
А	2.18	2.28	2.38	
A1	0.00		0.13	
b	0.63	0.76	0.89	
b2	0.72	0.93	1.14	
b3	4.57	5.02	5.46	
С	0.46	0.54	0.61	
c2	0.46	0.54	0.61	
D	5.97	6.10	6.22	
E	6.35	6.54	6.73	
е	:	2.29 BSC		
Н	9.40	9.91	10.41	
L	1.40	1.59	1.78	
L1	2.90 REF			
L2	0.51 BSC			
L3	0.89		1.27	
L4			1.01	
Z	3.93			











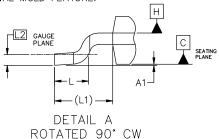
BOTTOM VIEW

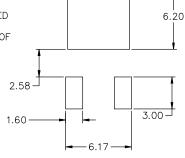
ALTERNATE CONSTRUCTIONS

#### NOTES:

- DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.

- CONTROLLING DIMENSION: MILLIMETERS.
  THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR
  BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15mm PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H. OPTIONAL MOLD FEATURE.





-5.80

RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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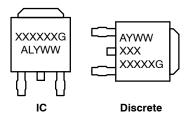
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#### DPAK3 6.10x6.54x2.28, 2.29P

CASE 369C ISSUE J

**DATE 12 AUG 2025** 

## GENERIC MARKING DIAGRAM\*



XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. COLLECTOR	2. DRAIN	2. CATHODE	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>EMITTER</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	4. DRAIN	<ol><li>CATHODE</li></ol>	4. ANODE	<ol><li>ANODE</li></ol>

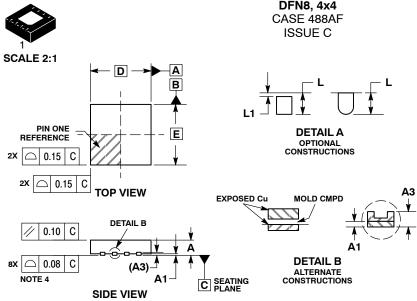
STYLE 6: PIN 1. MT1 2. MT2 3. GATE	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER	STYLE 8: PIN 1. N/C 2. CATHODE 3. ANODE	PIN 1. ANODE 2. CATHODE 3. RESISTOR ADJUST	STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE
4. MT2	<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	4. CATHODE	<ol><li>ANODE</li></ol>

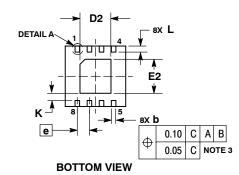
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DESCRIPTION:	DPAK3 6.10x6.54x2.28, 2.2	9P	PAGE 2 OF 2		

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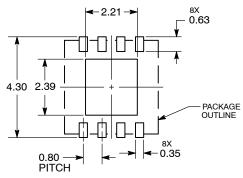
**DATE 15 JAN 2009** 







#### **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

## **DFN8, 4x4**

NOTES:

- DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
- 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.30MM FROM TERMINAL TIP.
  COPLANARITY APPLIES TO THE EXPOSED
- PAD AS WELL AS THE TERMINALS.
  DETAILS A AND B SHOW OPTIONAL CON-STRUCTIONS FOR TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.80	1.00		
A1	0.00	0.05		
А3	0.20	REF		
b	0.25	0.35		
D	4.00	BSC		
D2	1.91	2.21		
E	4.00	BSC		
E2	2.09	2.39		
е	0.80	BSC		
K	0.20			
L	0.30	0.50		
L1		0.15		

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot Т Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	DFN8, 4X4, 0.8P		PAGE 1 OF 1		

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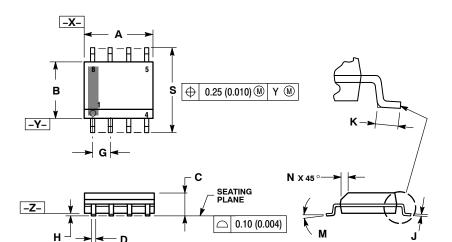
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





#### SOIC-8 NB CASE 751-07 **ISSUE AK**

**DATE 16 FEB 2011** 



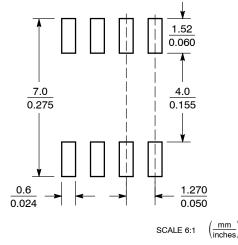
XS

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

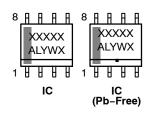
#### **SOLDERING FOOTPRINT\***

0.25 (0.010) M Z Y S



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week W

= Pb-Free Package

XXXXXX XXXXXX AYWW AYWW H  $\mathbb{H}$ Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α ww = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

#### **DATE 16 FEB 2011**

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	7. BASE, #1 8. EMITTER, #1  STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15:  PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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